

**Silicon PNP Power Transistors**

**2SB548**

**DESCRIPTION**

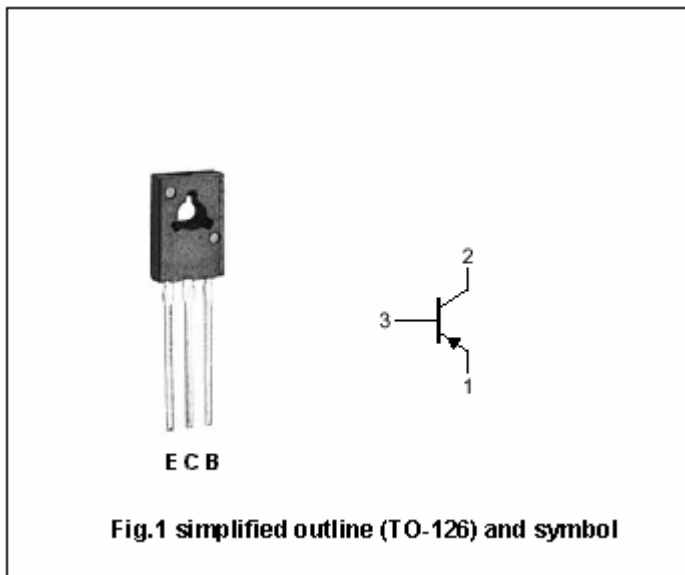
- With TO-126 package
- Complement to type 2SD414

**APPLICATIONS**

- Designed for use in driver and output stages of audio frequency amplifiers

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



**Absolute maximum ratings(Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-100	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-80	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current (DC)		-0.8	A
P <sub>D</sub>	Total power dissipation	T <sub>a</sub> =25	1.0	W
		T <sub>C</sub> =25	10	
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA ; I <sub>B</sub> =0	-80			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-50 μ A ; I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-0.5A ; I <sub>B</sub> =-50mA			-2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-0.5A ; I <sub>B</sub> =-50mA			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-80V ; I <sub>E</sub> =0			-1.0	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V ; I <sub>C</sub> =0			-1.0	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-0.2A ; V <sub>CE</sub> =-5V	40		320	
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V ; f=1MHz		25		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.1A ; V <sub>CE</sub> =-5V		70		MHz

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PACKAGE OUTLINE

